

Abstract Of The Disclosure

A method for producing etched holes and/or etched trenches of components based on silicon and/or a layered silicon/insulator structure. A germanium-containing layer and/or a germanium layer is provided at the point in the etching direction at which or
5 in whose surroundings an etching procedure is to be completed. Germanium and/or germanium compounds are detected during the etching procedure and the etching procedure is controlled, in particular interrupted, as a function of the detection of germanium and/or germanium compounds. In addition, a diaphragm sensor unit is provided, in whose layered structure a germanium and/or germanium-containing
10 layer is provided.